

# Modulated Wideband Power Amplifier

## 1 Introduction

The TBMDA4B modulated wideband power amplifier is designed in order to create an inexpensive signal source for immunity testing of electronic building blocks and products. It is designed to be driven by the tracking generator output of spectrum analyzers. With an input power range of -20 dBm...-10 dBm, it can boost the output power of a tracking generator up to 5W. With a frequency range from 100 kHz to 75 MHz, it is an ideal complement to the TBMDA3, which covers 10 MHz to 1 GHz. The TBMDA4B is ideal to drive Tekbox near field probes in order to find the sensitive spot of an electronic circuit or to create electric fields up to 550V/m when driving the Tekbox TEM Cell TBTC0, 300V/m when driving the TBTC1, 150V/m when driving the TBTC2 or 100V/m when driving the TBTC3. Test signals for immunity testing can be CW, AM or PM modulated. Consequently, the TBMDA4B provides built in modulation capability to generate 1 kHz AM or PM signals. In PM mode, the TBMDA4B can also generate a 217 Hz Signal with 12.5% duty cycle in order to simulate mobile phone TDMA noise.



Picture 1 – TBMDA4B modulated wideband driver amplifier, front view



Picture 2 – TBMDA4B modulated wideband driver amplifier, rear view

# Modulated Wideband Power Amplifier

## **Application:**

General-purpose power amplifier

Signal source for immunity testing, driving near field probes

Signal source for immunity testing, driving TEM Cells

## **Features:**

CW amplifier (modulation off)

1 kHz, 80% AM modulation

1 kHz, 50% duty cycle pulse modulation

217 Hz, 12.5% duty cycle pulse modulation

## 2 Electrical Specifications

### **Technical Data:**

Input / Output: 50 Ohm, N female

Supply Voltage range: 110 V...240 V

Supply power consumption: 20 W

Operating temperature range: -20°C to 50°C

Frequency range: 100 kHz – 75 MHz

Saturated output power @ 100 kHz / Pin = -10 dBm: 36.6 dBm (4.6W) typ.

Saturated output power @ 1 MHz / Pin = -10 dBm: 37.6 dBm (5.8W) typ.

Saturated output power @ 10 MHz / Pin = -10 dBm: 37.6 dBm (5.8W) typ.

Saturated output power @ 35 MHz / Pin = -10 dBm: 37.1 dBm (5.1W) typ.

Saturated output power @ 75 MHz / Pin = -10 dBm: 36.6 dBm (4.6W) typ.

Saturated output power @ 100 MHz / Pin = -10 dBm: 31.6 dBm (1.4W) typ.

1dB output compression point @ 1 MHz: +35.7 dBm typ.

1dB output compression point @ 35 MHz: +34.8 dBm typ.

1dB output compression point @ 75 MHz: +34.1 dBm typ.

2<sup>nd</sup> harmonic, 35 MHz, Pout=36dBm: < - 18 dBc typ.

2<sup>nd</sup> harmonic, 35 MHz, Pout=30dBm: < - 21 dBc typ.

3<sup>rd</sup> harmonic, 35 MHz, Pout=36dBm: < - 19 dBc typ.

3<sup>rd</sup> harmonic, 35 MHz, Pout=30dBm: < - 35 dBc typ.

Total harmonic distortion:

5.9% @35MHz, Pout=27dBm typ.

8.4% @35 MHz, Pout=30 dBm typ.

12.3% @35 MHz, Pout=33 dBm typ.

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18.1% @35 MHz, Pout=36 dBm typ.

Third order intercept point: +53dBm, @25 MHz,  $\Delta f = 200\text{kHz}$  typ.

Noise figure @35 MHz: 7.2 dB

Internal modulation frequency AM: 1 kHz  $\pm 20\%$

Internal modulation frequencies PM: 1 kHz  $\pm 10\%$ , 217 Hz  $\pm 20\%$

Duty cycle, PM: 50%  $\pm 10\%$  @ 1 kHz; 12.5%  $\pm 20\%$  @ 217 Hz

### Maximum ratings:

Maximum input power: 0 dBm

The output of the TBMDA4B is quite tolerant to output mismatch, however open or shorted load is not recommended, as it potentially can cause damage. When driving near field probes or current probes, it is highly recommended to insert a 3dB attenuator at the output of the amplifier in order to protect the output stage.

### Small Signal Performance (@ Pin = -30 dBm):

Frequency [MHz]	0.05	0.075	0.1	0.25	0.5	0.75	1	5	10	25	50	75	100
Output power [dBm]	17.5	20.2	21.2	23.1	23.4	23.7	23.7	23.9	23.9	23.8	22.6	21.7	17.6
Gain [dB]	47.5	50.2	51.2	53.1	53.4	53.7	53.7	53.9	53.9	53.8	52.6	51.7	47.6

Table 1 – TBMDA4B small signal gain

### Linear output power (@ Pin = -22 dBm):

Frequency [MHz]	0.05	0.075	0.1	0.25	0.5	0.75	1	5	10	25	50	75	100
Output power [dBm]	25.4	28.1	29.3	31.1	31.4	31.7	31.7	31.9	31.9	31.8	30.5	29.7	25.6
Gain [dB]	47.4	50.1	51.3	53.1	53.4	53.7	53.7	53.9	53.9	53.8	52.5	51.7	47.6

Table 2 – TBMDA4B, linear output power versus frequency, 50 kHz – 100 MHz

### 1 dB compression point (@ Pin = -17 dBm):

Frequency [MHz]	0.05	0.075	0.1	0.25	0.5	0.75	1	5	10	25	50	75	100
Output power [dBm]	30.2	32.8	33.9	35.4	35.4	35.8	36	36	36	35.9	34.7	34.1	29.5
Gain [dB]	47.2	49.8	50.9	52.4	52.4	52.8	53	53	53	52.9	51.7	51.1	46.5

Table 3 – TBMDA4B, 1 dB compression point versus frequency, 50 kHz – 100 MHz

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## Saturation (@ Pin = -10 dBm):

Frequency [MHz]	0.05	0.075	0.1	0.25	0.5	0.75	1	5	10	25	50	75	100
Output power [dBm]	34.4	36.1	36.7	37.4	37.1	37.6	37.6	37.6	37.6	37.4	36.8	36.6	31.6
Gain [dB]	44.4	46.1	46.7	47.4	47.1	47.6	47.6	47.6	47.6	47.4	46.8	46.6	41.6

Table 3 – TBMDA4B, Saturation versus frequency, 50 kHz – 100 MHz

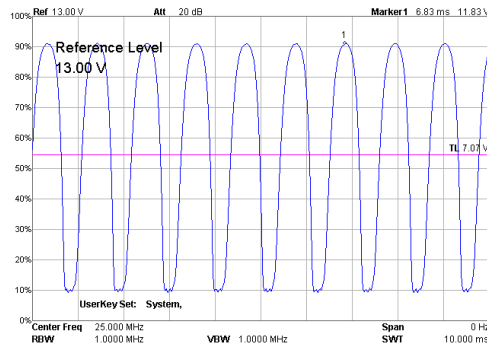


Figure 1 – 1 kHz, 80 % AM envelope, 25 MHz

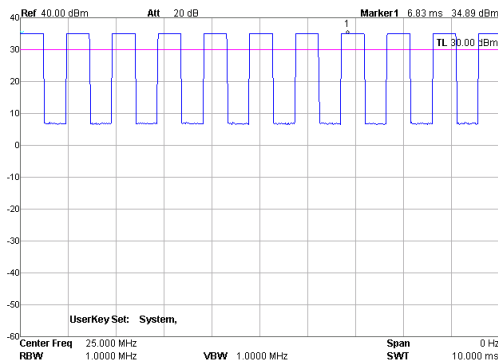


Figure 2 – 1 kHz, 50 % PM envelope, 25 MHz

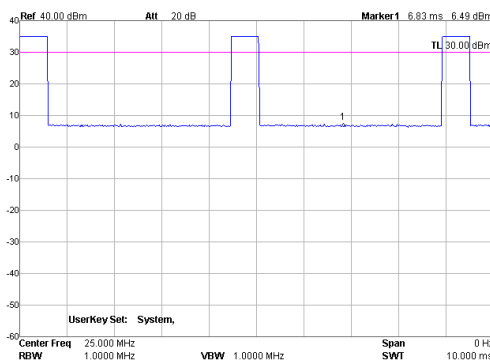


Figure 3 – 217 Hz, 12.5 % PM envelope, 25 MHz

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### 3 Applications

#### Immunity testing using a TEM cell

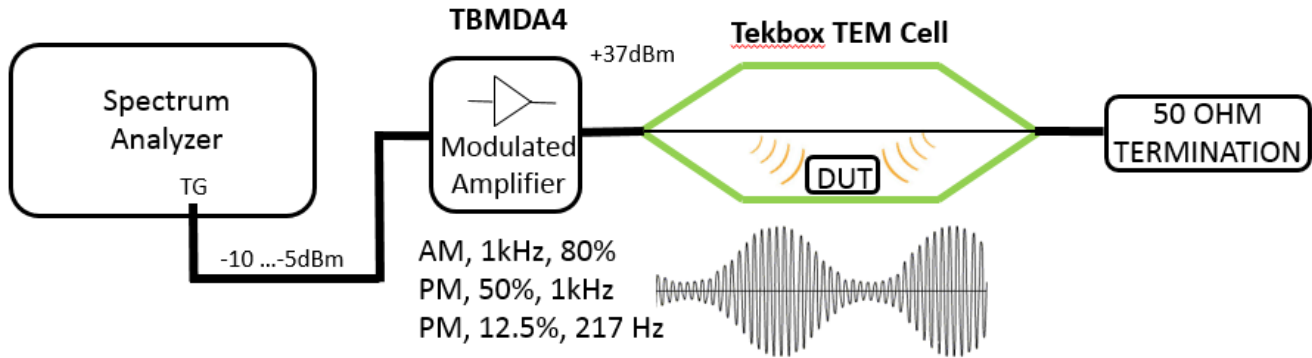


Figure 4 – immunity testing set up

#### Immunity testing using near field probes

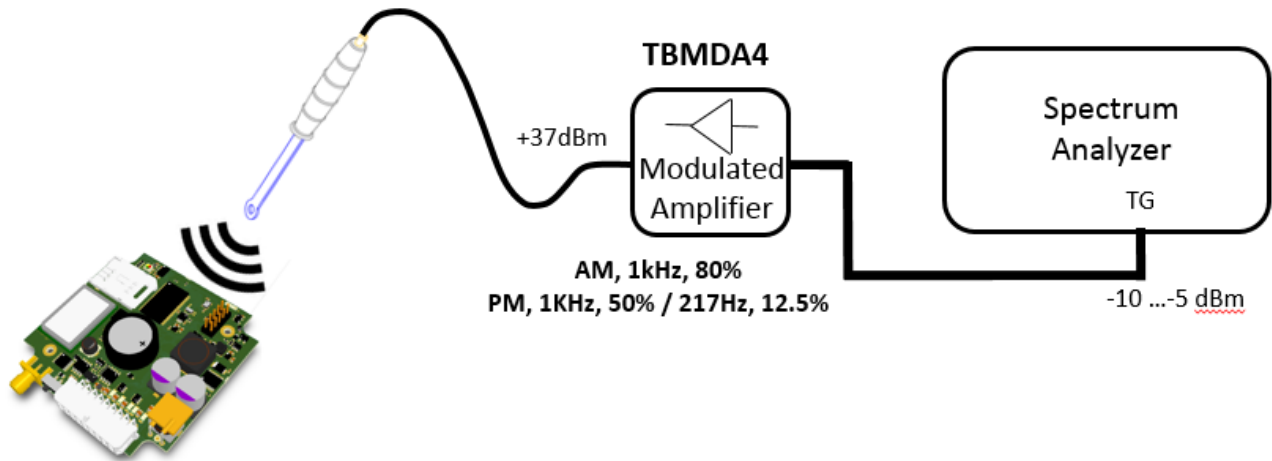


Figure 5 – immunity testing set up

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### 4 TEM Cell field strength

A typical pre compliance set up for immunity testing is typically not sophisticated enough to measure the real field strength inside the TEM cell. However, the field strength can be approximated mathematically.

The E-field (V/m) between septum and lower (upper) wall of a TEM cell is  $E = V/d$  where V is the RMS voltage of the applied signal and d is the distance between septum and lower (upper) wall. This is based on the simplified assumption that the E field would be perfectly homogenous/evenly distributed. A more practical formula is  $E = V*Cor/d$  where Cor is a correction factor for the average field strength over the volume of the DUT derived from the analysis of the field distribution over the cross section of the cell.

Assuming the DUT is placed in the center of the cell and in the middle between bottom wall and septum, we can however use the simplified formula with sufficient accuracy.

$$TBTC0: d = 2.8 \text{ cm} \rightarrow E_{[V/m]} = (\sqrt{P*50\Omega}) * 35.7$$

$$TBTC1: d = 5 \text{ cm} \rightarrow E_{[V/m]} = (\sqrt{P*50\Omega}) * 20$$

$$TBTC2: d = 10 \text{ cm} \rightarrow E_{[V/m]} = (\sqrt{P*50\Omega}) * 10$$

$$TBTC3: d = 15 \text{ cm} \rightarrow E_{[V/m]} = (\sqrt{P*50\Omega}) * 6.66$$

The power P in the formulas above has to be entered in [Watt]

$$P_{[W]} = 0.001 * (10^{(P_{[dBm]}/10)})$$

Frequency [MHz]	Input power [dBm]	Output power [dBm]	Field strength TBTC0 [V/m]	Field strength TBTC1 [V/m]	Field strength TBTC2 [V/m]	Field strength TBTC3 [V/m]
0.05	-10	34.4	419	235	117	78
0.1	-10	36.7	546	306	153	102
0.5	-10	37.1	572	320	160	107
1	-10	37.6	606	339	170	113
5	-10	37.6	606	339	170	113
10	-10	37.6	606	339	170	113
25	-10	37.4	592	332	166	111
50	-10	36.8	552	309	155	103
75	-10	36.6	540	302	151	101

Table 3 – calculated field strength for TBMDA4B driving Tekbox TEM cells

## Modulated Wideband Power Amplifier

### 5 PC Software for immunity testing

The Tekbox EMCview SW is regularly updated and now supports immunity testing with a feature for automated tracking generator control. This significantly simplifies immunity testing, especially in case of repeated testing during validation of DUT modifications/improvements.

Tekbox EMCview currently supports Rigol, Siglent, R&S FPC and FPH series spectrum analyzers.

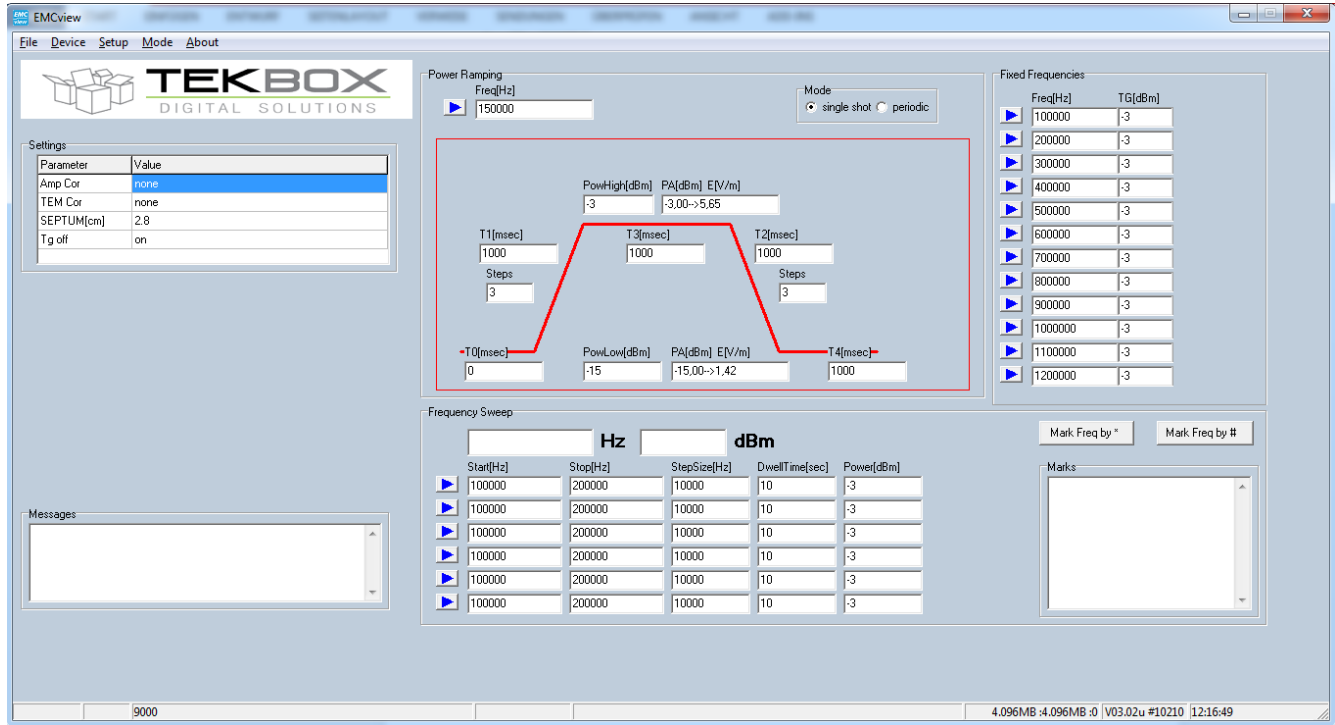


Figure 8 – screenshot of the tracking generator control feature of EMCview

### **WARNING:**

**Never connect the output of the TBMDA4B directly to the input of a spectrum analyzer. Check the maximum input ratings of the spectrum analyzer and protect it with an appropriate attenuator. Open or shorted load is not recommended, potentially can cause damage of the RF output stage.**

### **Example:**

**Rigol DSA815 – maximum input power rating: +20dBm**

## Modulated Wideband Power Amplifier

### 6 Ordering Information

Part Number	Description
TBMDA4B-EU	modulated power amplifier, 2 pcs 75cm N-male to N-male cables, 1 pc 30dB / 10W attenuator with N-connectors, C13 Schuko power cord
TBMDA4B-US	modulated power amplifier, 2 pcs 75cm N-male to N-male cables, 1 pc 30dB / 10W attenuator with N-connectors, C13 US power cord
TBMDA4B-UK	modulated power amplifier, 2 pcs 75cm N-male to N-male cables, 1 pc 30dB / 10W attenuator with N-connectors, C13 English power cord
TBMDA4B-AU	modulated power amplifier, 2 pcs 75cm N-male to N-male cables, 1 pc 30dB / 10W attenuator with N-connectors, C13 Australian power cord

Table 5 – Ordering Information

### 7 History

Version	Date	Author	Changes
V1.0	14.4.2021	Mayerhofer	Creation of the document
V1.1	24.6.2021	Hoa Hoang	Update product picture

Table 6 – History

[www.tekbox.com](http://www.tekbox.com)

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